

## United States Patent [19]

## **Park**

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**Patent Number:** [11]

6,147,926

**Date of Patent:** 

Nov. 14, 2000

[54]	SEMICONDUCTOR MEMORY DEVICE
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[21]	Appl. No.: 09/318,838
[22]	Filed: May 26, 1999
[30]	Foreign Application Priority Data
Dec. 29, 1998 [KR] Rep. of Korea 98-60417	
	Int. Cl. <sup>7</sup>
[58]	Field of Search
[56]	References Cited
	U.S. PATENT DOCUMENTS

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Primary Examiner—Huan Hoang Attorney, Agent, or Firm-Morgan, Lewis & Bockius LLP **ABSTRACT** 

Semiconductor memory device which can support a DDR SDRAM latency mode like 2.5 for easy application to a high data rate memory, including a memory cell array having a plurality of memory cell regions for storing external data and forwarding the data on two lines by a decoded column address, a data path unit for forwarding the data from the memory cell array received through the two lines outwardly synchronous to an edge of internal clock, a controlling unit for controlling the data path unit entirely, a FIFO unit for controlling a forwarding order of the two data received from the data path unit, a latency pipeline controlling unit for providing an Enable signal for setting a data output enable interval at each of the control unit and the data path unit, a clock generating unit for providing the internal clock to the FIFO unit, the data path unit and the latency pipeline controlling unit for obtaining a desired band width, and a burst counter for providing a read signal having information on a burst length to the FIFO unit and the latency pipeline control unit.

## 10 Claims, 9 Drawing Sheets

